ABSTRACT OF THE DISCLOSURE

The present invention relates to a bonding pad of a semiconductor device and a formation method thereof, and the object of the present invention is to prevent bonding defects by enlarging contact area between a bonding pad and a soldering material and to prevent moisture from penetrating into an oxide layer. The present invention provides a bonding pad of a semiconductor device comprising: a barrier metal layer formed on a structure of a semiconductor substrate; a metal wire layer formed on the barrier metal layer; a passivation metal layer formed on the metal wire layer and removed partly to expose a portion of the upper surface of the metal wire layer; an insulating layer which is formed on the passivation metal layer and has a contact hole exposing the metal wire layer via the portion that the passivation metal layer is removed; and an adhesive metal layer formed on the inner surface of the contact hole.